

**Silicon NPN Power Transistor**

**2SC4580**

**DESCRIPTION**

- Collector-Emitter Sustaining Voltage-  
 :  $V_{CEO(SUS)} = 450V(\text{Min})$
- Fast Switching speed

**APPLICATIONS**

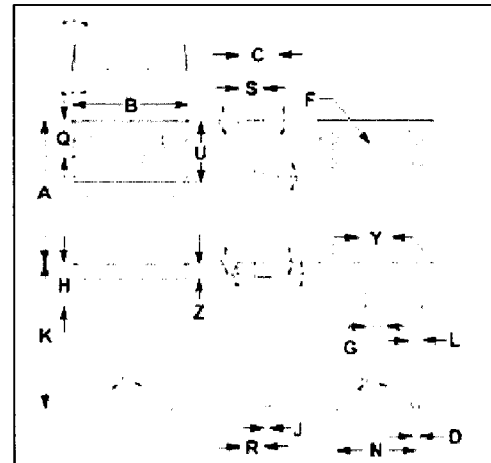
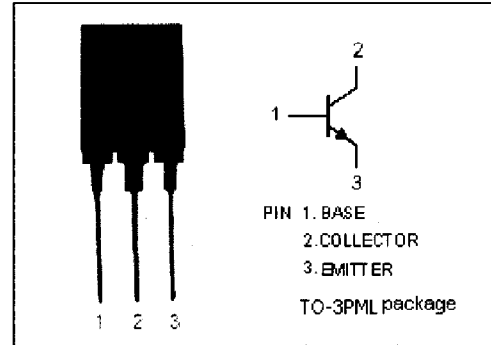
- Designed for power switching applications.

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

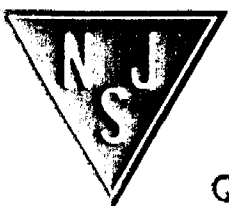
SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	600	V
$V_{CEO}$	Collector-Emitter Voltage	450	V
$V_{CEX}$	Collector-Emitter Voltage $V_{EB} = 5V$	600	V
$V_{EBO}$	Emitter-Base Voltage	7	V
$I_C$	Collector Current-Continuous	8	A
$I_{CM}$	Collector Current-Peak	16	A
$I_B$	Base Current-Continuous	4	A
$I_{BM}$	Base Current-Peak	8	A
$P_T$	Total Power Dissipation @ $T_c = 25^\circ\text{C}$	50	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th J-C}$	Thermal Resistance, Junction to Case	2.5	$^\circ\text{C/W}$



DIM	mm	
	MIN	MAX
A	19.90	20.10
B	15.90	16.10
C	5.50	5.70
D	0.90	1.10
F	3.30	3.50
G	2.90	3.10
H	5.90	6.10
J	0.595	0.605
K	22.30	22.50
L	1.90	2.10
N	10.80	11.00
Q	4.90	5.10
R	3.75	3.95
S	3.20	3.40
U	9.90	10.10
Y	4.70	4.90
Z	1.90	2.10



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## ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=0.2\text{A}; I_B=0$	450			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=4\text{A}; I_B=0.8\text{A}$			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=4\text{A}; I_B=0.8\text{A}$			1.5	V
$I_{CBO}$	Collector Cutoff Current	At rated Voltage			100	$\mu\text{A}$
$I_{CEO}$	Collector Cutoff Current	At rated Voltage			100	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	At rated Voltage			100	$\mu\text{A}$
$h_{FE-1}$	DC Current Gain	$I_C=4\text{A}; V_{CE}=5\text{V}$	10			
$h_{FE-2}$	DC Current Gain	$I_C=1\text{mA}; V_{CE}=5\text{V}$	5			
$f_T$	Current-Gain—Bandwidth Product	$I_C=0.8\text{A}; V_{CE}=10\text{V}$		20		MHz

### Switching times

$t_{on}$	Turn-on Time	$I_C=4\text{A}; I_{B1}=0.8\text{A}; I_{B2}=-1.6\text{A}$ $R_L=37.5\ \Omega; V_{BB2}=4\text{V}$			0.5	$\mu\text{s}$
$t_{stg}$	Storage Time				2.0	$\mu\text{s}$
$t_f$	Fall Time				0.2	$\mu\text{s}$